

**Silicon NPN Power Transistors**

**2SC1617**

**DESCRIPTION**

- With TO-3 package
- High voltage:  $V_{CBO(min)}$ :300V
- Wide safe oprating area

**APPLICATIONS**

- For B/W white TV horizontal output applications

**PINNING(see fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

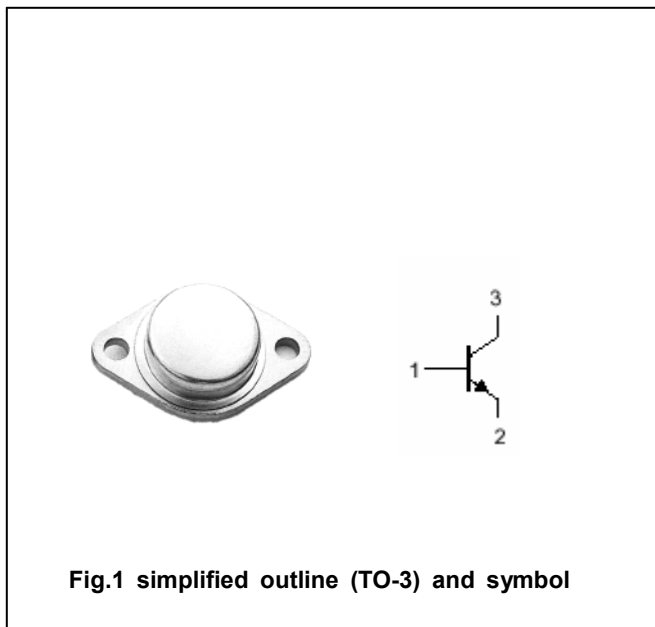


Fig.1 simplified outline (TO-3) and symbol

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	100	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		7	A
$I_E$	Emitter current		-7	A
$P_C$	Collector power dissipation	$T_C=25^\circ C$	50	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0	100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5 A			1.2	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =250V; I <sub>E</sub> =0			1.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	30		150	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =7A; V <sub>CE</sub> =5V	15			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V		10		MHz

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PACKAGE OUTLINE

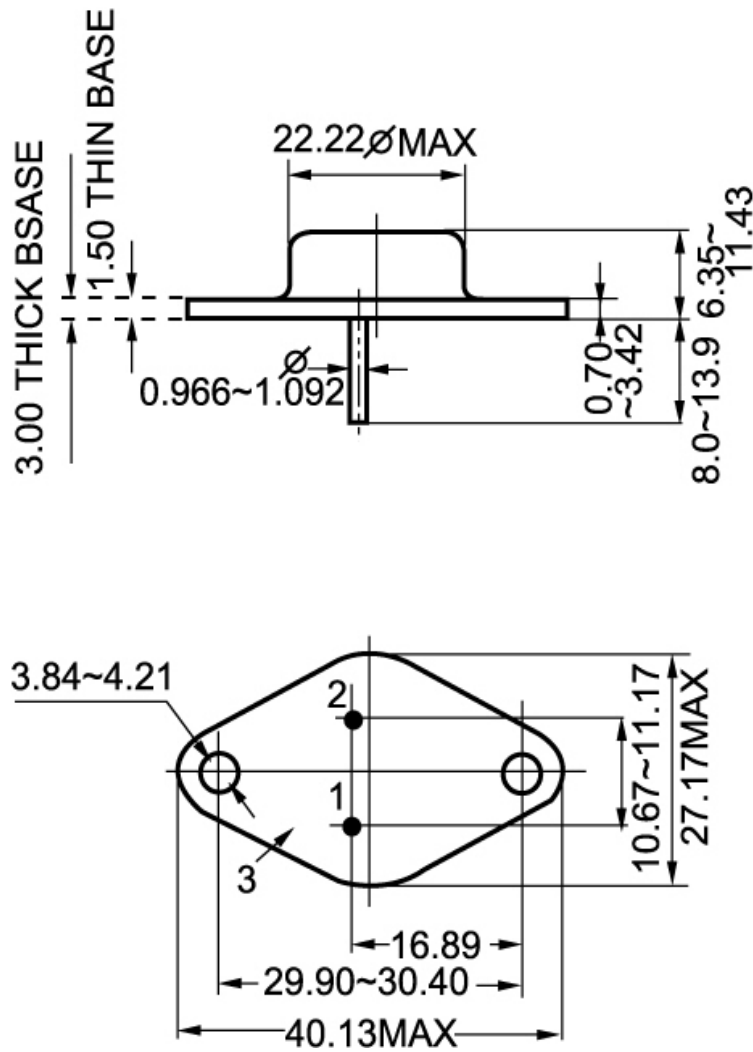


Fig.2 Outline dimensions